

IRF7402

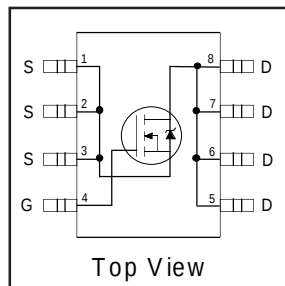
HEXFET® Power MOSFET

- Generation V Technology
- Ultra Low On-Resistance
- N-Channel MOSFET
- Very Small SOIC Package
- Low Profile (<1.1mm)
- Available in Tape & Reel
- Fast Switching

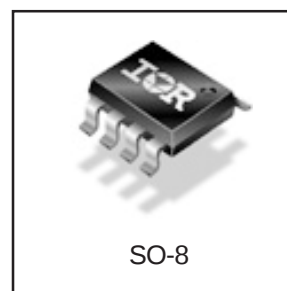
Description

Fifth Generation HEXFET® power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The SO-8 has been modified through a customized leadframe for enhanced thermal characteristics and multiple-die capability making it ideal in a variety of power applications. With these improvements, multiple devices can be used in an application with dramatically reduced board space. The package is designed for vapor phase, infrared or wave soldering techniques. Power dissipation of greater than 0.8 W is possible in a typical PCB mount application.



$V_{DS} = 20V$
$R_{DS(on)} = 0.035\Omega$



Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ $T_A = 25^\circ C$	Continuous Drain Current, V_{GS} @ 4.5V	6.8	A
I_D @ $T_A = 70^\circ C$	Continuous Drain Current, V_{GS} @ 4.5V	5.4	
I_{DM}	Pulsed Drain Current ①	54	
P_D @ $T_A = 25^\circ C$	Power Dissipation	2.5	W
P_D @ $T_A = 70^\circ C$	Power Dissipation	1.6	
	Linear Derating Factor	0.02	W/°C
V_{GS}	Gate-to-Source Voltage	± 12	V
dv/dt	Peak Diode Recovery dv/dt ②	5.0	V/ns
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	°C

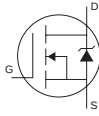
Thermal Resistance

	Parameter	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient ④	50	°C/W

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	20	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.024	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.035	Ω	$V_{GS} = 4.5V, I_D = 4.1A$ ③
		—	—	0.050		$V_{GS} = 2.7V, I_D = 3.5A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	0.70	—	—	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
g_{fs}	Forward Transconductance	6.1	—	—	S	$V_{DS} = 10V, I_D = 1.9A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	1.0	μA	$V_{DS} = 16V, V_{GS} = 0V$
		—	—	25		$V_{DS} = 16V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 12V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -12V$
Q_g	Total Gate Charge	—	14	22	nC	$I_D = 3.8A$
Q_{gs}	Gate-to-Source Charge	—	2.0	3.0		$V_{DS} = 16V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	6.3	9.5		$V_{GS} = 4.5V$, See Fig. 6 and 12 ③
$t_{d(on)}$	Turn-On Delay Time	—	5.1	—	ns	$V_{DD} = 10V$
t_r	Rise Time	—	47	—		$I_D = 3.8A$
$t_{d(off)}$	Turn-Off Delay Time	—	24	—		$R_G = 6.2\Omega$
t_f	Fall Time	—	32	—		$R_D = 2.6\Omega$ ③
C_{iss}	Input Capacitance	—	650	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	300	—		$V_{DS} = 15V$
C_{rss}	Reverse Transfer Capacitance	—	150	—		$f = 1.0MHz$, See Fig. 5

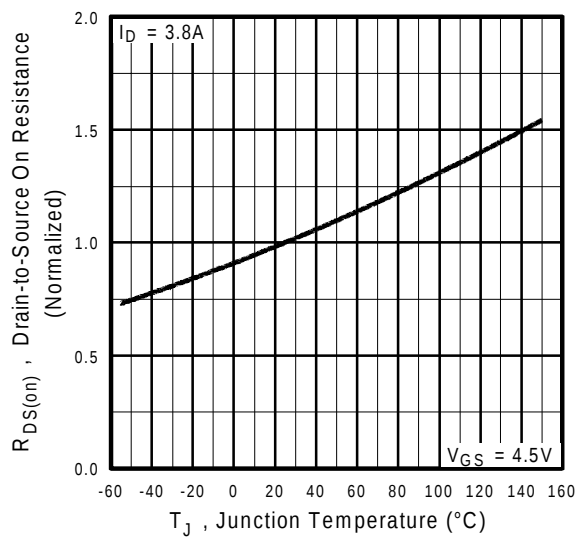
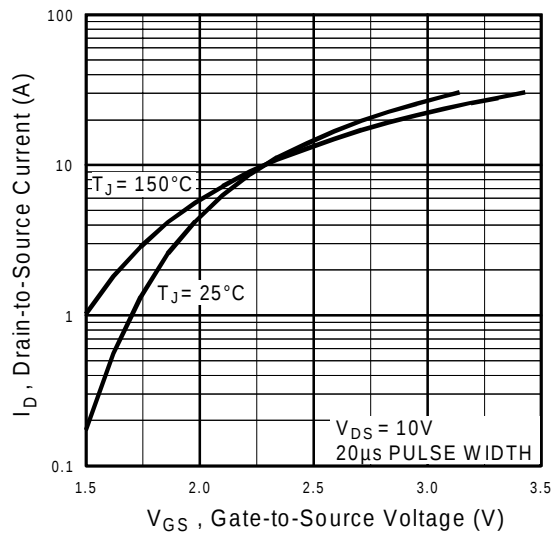
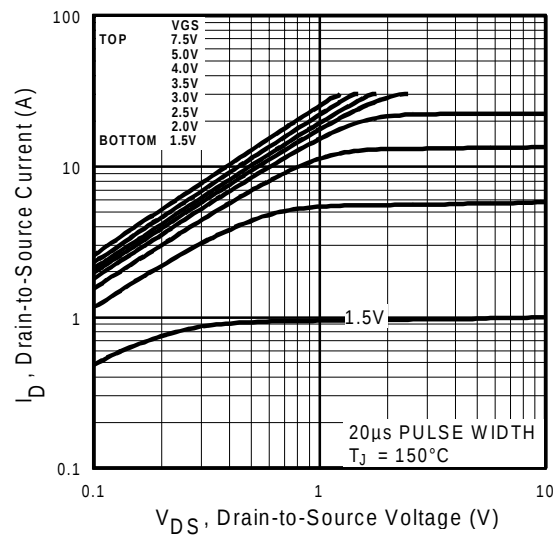
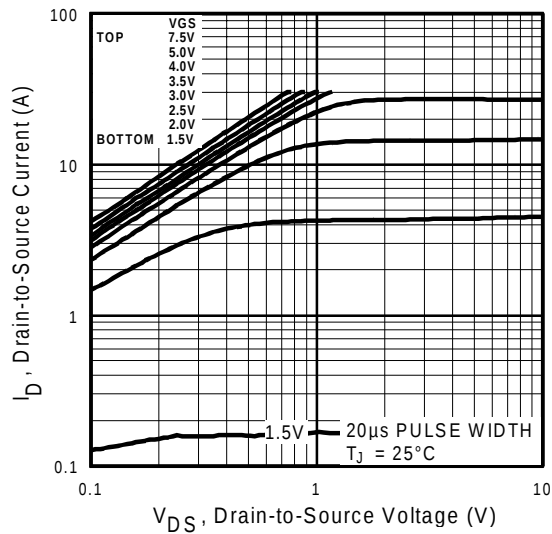
Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	2.5	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	54		
V_{SD}	Diode Forward Voltage	—	—	1.2	V	$T_J = 25^\circ\text{C}, I_S = 3.8A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	51	77	ns	$T_J = 25^\circ\text{C}, I_F = 3.8A$
Q_{rr}	Reverse Recovery Charge	—	69	100	nC	$di/dt = 100A/\mu s$ ③

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② $I_{SD} \leq 3.8A$, $di/dt \leq 96A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 150^\circ\text{C}$

- ③ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.
- ④ When mounted on 1 inch square copper board, $t \leq 10$ sec
- ⑤ This data sheet has curves & data from IRF7601



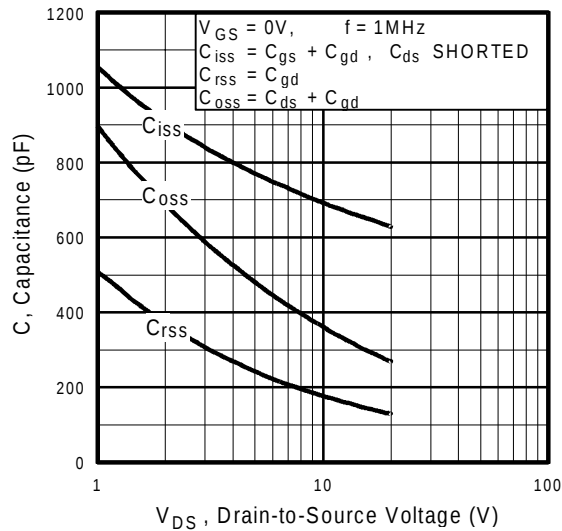


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

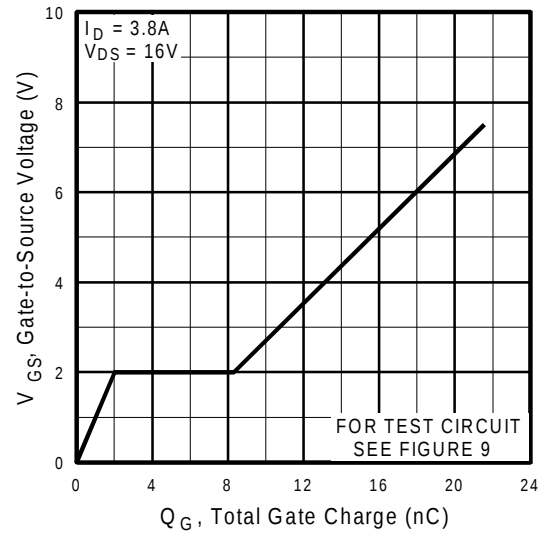


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

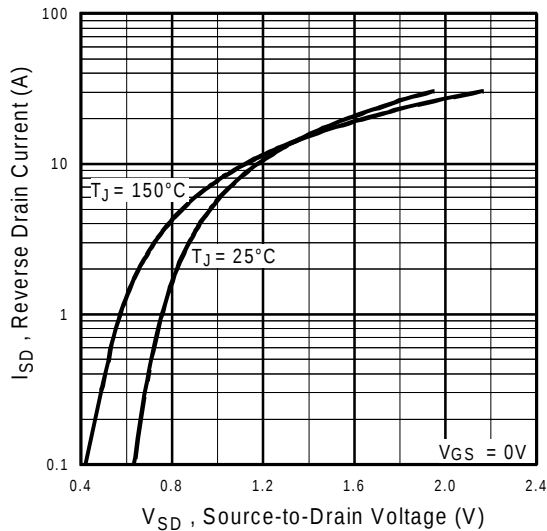


Fig 7. Typical Source-Drain Diode Forward Voltage

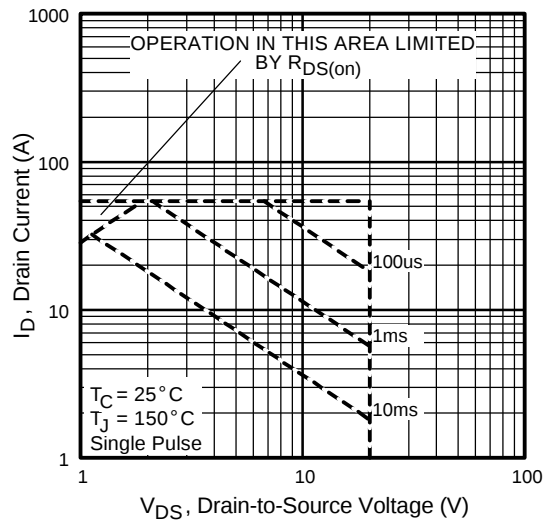


Fig 8. Maximum Safe Operating Area

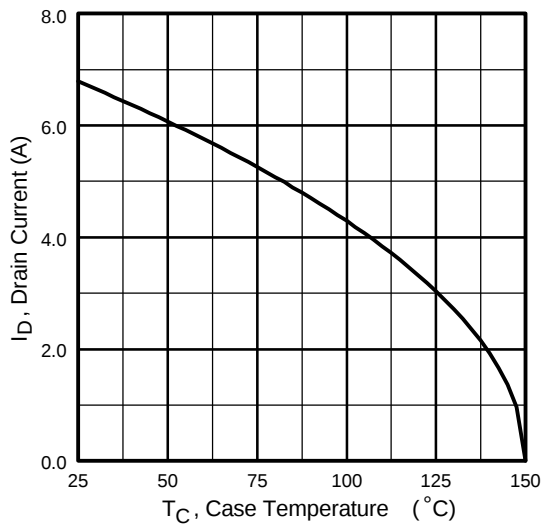


Fig 9. Maximum Drain Current Vs. Ambient Temperature

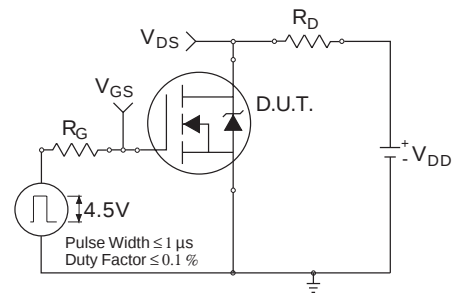


Fig 10a. Switching Time Test Circuit

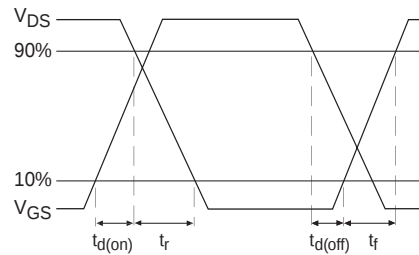


Fig 10b. Switching Time Waveforms

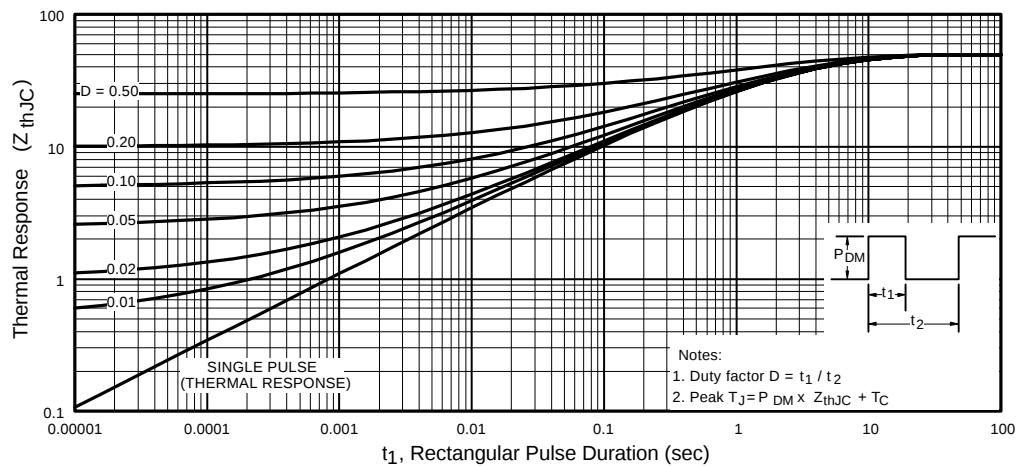


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

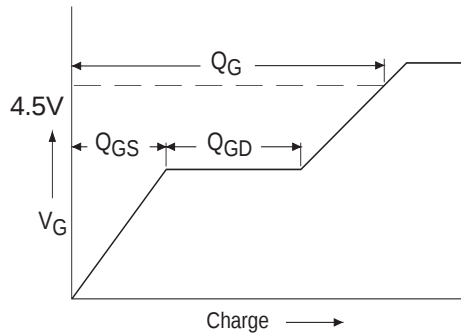


Fig 12a. Basic Gate Charge Waveform

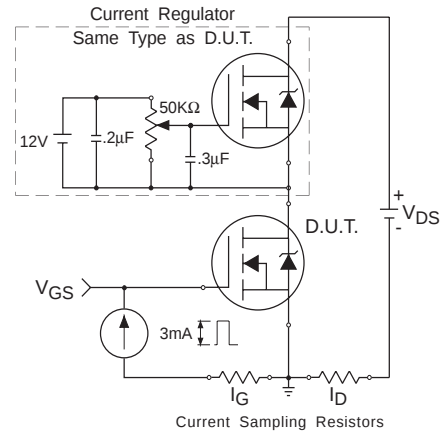


Fig 12b. Gate Charge Test Circuit

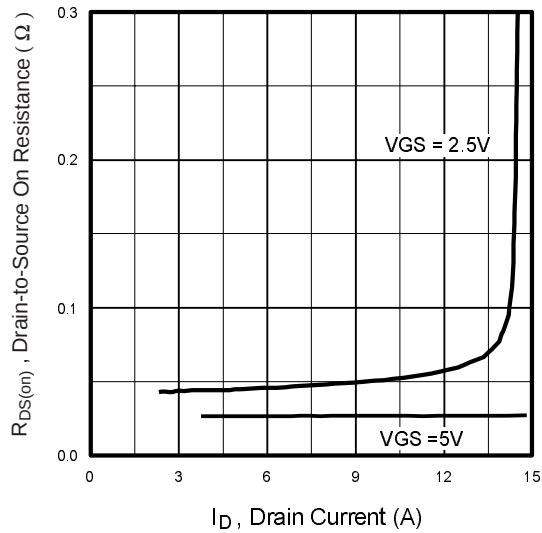


Fig 13. Typical On-Resistance Vs. Drain Current

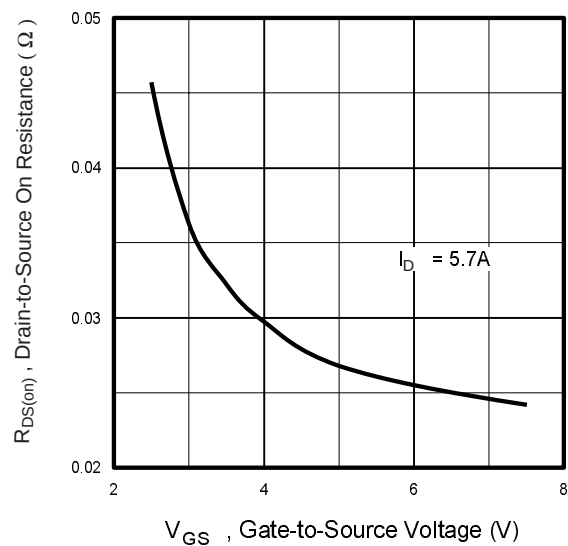
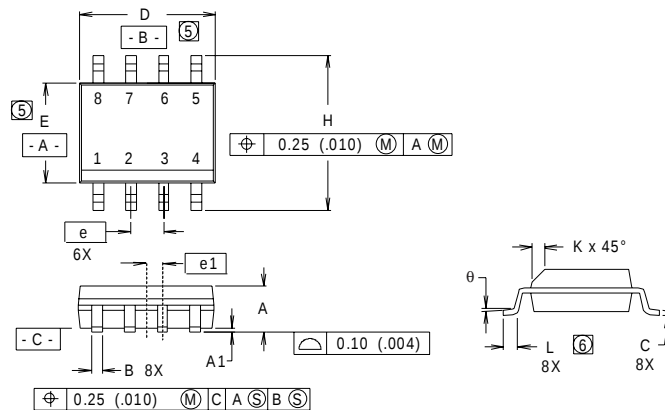


Fig 14. Typical On-Resistance Vs. Gate Voltage

SO-8 Package Details

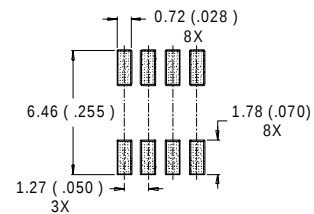


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1982.
2. CONTROLLING DIMENSION : INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- ⑤ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS
MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.006).
- ⑥ DIMENSIONS IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE..

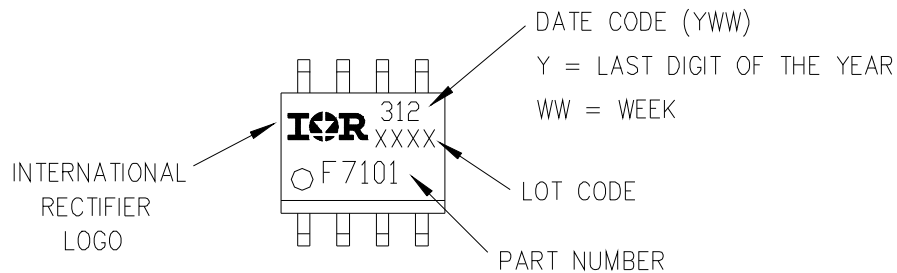
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
B	.014	.018	0.36	0.46
C	.0075	.0098	0.19	0.25
D	.189	.196	4.80	4.98
E	.150	.157	3.81	3.99
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.011	.019	0.28	0.48
L	0.16	.050	0.41	1.27
θ	0°	8°	0°	8°

RECOMMENDED FOOTPRINT



SO-8 Part Marking

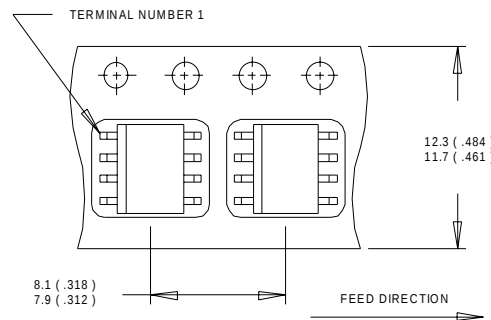
EXAMPLE: THIS IS AN IRF7101



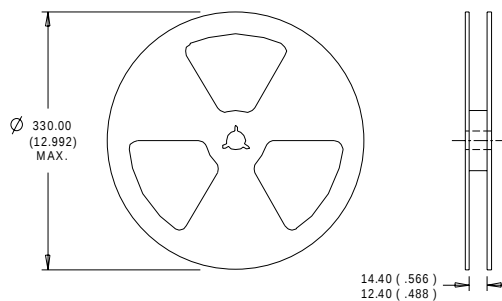
IRF7402

International
IR Rectifier

SO-8 Tape and Reel



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

International
IR Rectifier

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IR GERMANY: Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 6172 96590

IR ITALY: Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 11 451 0111

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Data and specifications subject to change without notice. 2/2000